# **Excellent Integrated System Limited**

Stocking Distributor

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<u>Vishay Semiconductor/Diodes Division</u> 8ETH03-1

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# Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite Datasheet of 8ETH03-1 - DIODE GEN PURP 300V 8A TO262

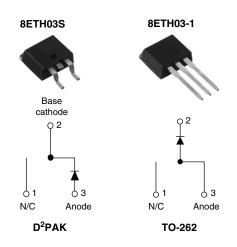
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### 8ETH03S/8ETH03-1

Vishay High Power Products

# Hyperfast Rectifier, 8 A FRED Pt<sup>TM</sup>



PRODUCT SUMMARY				
t <sub>rr</sub>	35 ns			
I <sub>F(AV)</sub>	8 A			
$V_{R}$	300 V			

#### **FEATURES**

- Hyperfast recovery time
- Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature
- · Designed and qualified for industrial level

#### **DESCRIPTION/APPLICATIONS**

300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, dc-to-dc converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Repetitive peak reverse voltage	$V_{RRM}$		300	V	
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 155 °C	8	^	
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>C</sub> = 25 °C	100	A	
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		- 65 to 175	°C	

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	300	-	-	
Forward voltage V <sub>F</sub>	I <sub>F</sub> = 8 A	-	1.0	1.25	V	
	I <sub>F</sub> = 8 A, T <sub>J</sub> = 125 °C	-	0.83	1.00		
Develop lastra as assessed		$V_R = V_R$ rated	-	0.02	20	
Reverse leakage current I <sub>R</sub>	IR.	T <sub>J</sub> = 125 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	6.0	200	μΑ
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 300 V -		31	-	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body - 8 -		nH		

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time		I <sub>F</sub> = 1 A, dI <sub>F</sub> /dt = - 50 A/μs, V <sub>R</sub> = 30 V		-	-	35	
	t <sub>rr</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 8 A dI <sub>F</sub> /dt = - 200 A/μs V <sub>R</sub> = 200 V	-	27	-	ns
		T <sub>J</sub> = 125 °C		-	40	-	
Peak recovery current		T <sub>J</sub> = 25 °C		-	2.2	-	A
	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	5.3	-	
Reverse recovery charge		T <sub>J</sub> = 25 °C		-	30	-	nC
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	106	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 65	-	175	°C
Thermal resistance, junction to case per leg	R <sub>thJC</sub>	R <sub>thJC</sub>		1.45	2.5	
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.2	-	
Weight			-	2.0	-	g
			-	0.07	-	OZ.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf ⋅ cm (lbf ⋅ in)
AA. disa da isa		Case style D <sup>2</sup> PAK	8ETH03S			
Marking device		Case style TO-262	8ETH03-1			



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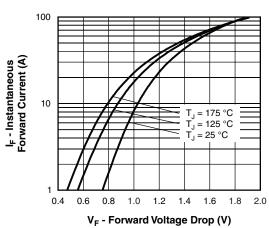


Fig. 1 - Typical Forward Voltage Drop Characteristics

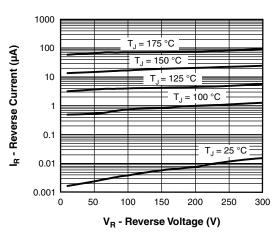


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

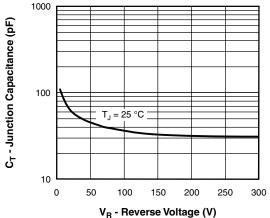


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

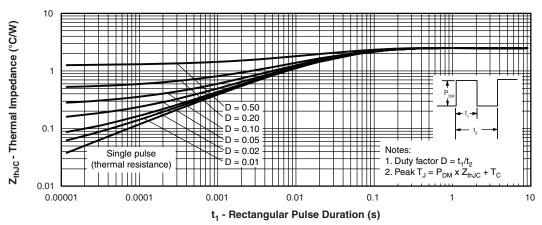


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

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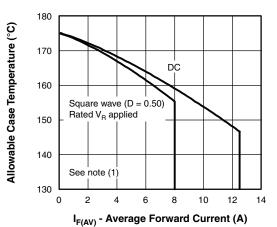


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

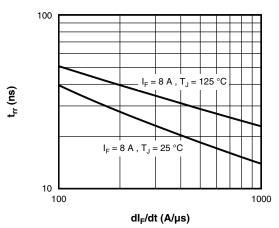


Fig. 7 - Typical Reverse Recovery Time vs.  $dI_F/dt$ 

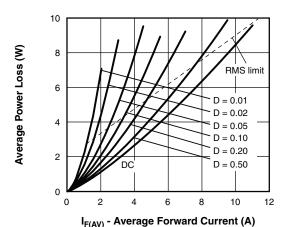


Fig. 6 - Forward Power Loss Characteristics

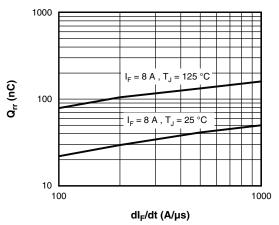


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $\begin{array}{l} \text{(1)} \ \ \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \ x \ R_{thJC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \ x \ V_{FM} \ \text{at } (I_{F(AV)}/D) \ \text{(see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \ x \ I_{R} \ (1 - D); \ I_{R} \ \text{at } V_{R1} = \text{Rated } V_{R} \\ \end{array}$ 



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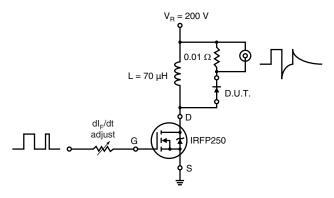
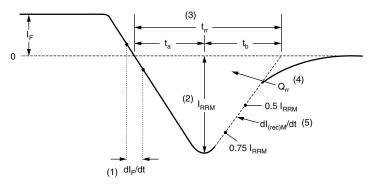


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dl_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 10 - Reverse Recovery Waveform and Definitions



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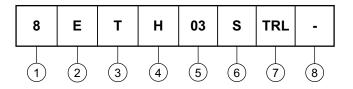
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#### **ORDERING INFORMATION TABLE**

**Device code** 



- Current rating (8 A)
- 2 E = Single diode
- 3  $T = TO-220, D^2PAK$
- 4 H = Hyperfast rectifier
- Voltage rating (03 = 300 V)
- 6 • S = D<sup>2</sup>PAK
  - -1 = TO-262
- 7 • None = Tube (50 pieces)
  - TRL = Tape and reel (left oriented, for D<sup>2</sup>PAK package)
  - TRR = Tape and reel (right oriented, for D<sup>2</sup>PAK package)
- 8 • None = Standard production
  - PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS				
Dimensions http://www.vishay.com/doc?95014				
Part marking information	http://www.vishay.com/doc?95008			
Packaging information	http://www.vishay.com/doc?95032			

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